IR-Lumineszenzdiode (850 nm) mit hoher Ausgangsleistung
High Power Infrared Emitter (850 nm)
Lead (Pb) Free Product - RoHS Compliant

SFH 4350

gemäß OS-PCN-2009-021-A2

acc. to OS-PCN-2009-021-A2

Wesentliche Merkmale

- Infrarot LED mit hoher Ausgangsleistung
- Abstrahlwinkel ± 13°
- Sehr hohe Strahlstärke
- Kurze Schaltzeiten
- UL Version erhältlich

Features

- High Power Infrared LED
- Emission angle ± 13°
- Very high radiant intensity
- Short switching times
- UL version available

Anwendungen

- Infrarotbeleuchtung für Kameras
- Sensorik
- Datenübertragung
- Rauchmelder

Applications

- Infrared Illumination for cameras
- Sensor technology
- Data transmission
- Smoke detectors

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheits-richtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Typ **Type**	**Bestellnummer** **Ordering Code**	**Strahlstärkegruppierung**[1] (I_F = 100 mA, t_p = 20 ms) **Radiant Intensity Grouping**[1] I_e (mW/sr)
SFH 4350	Q65110A2091	≥ 63 (typ. 200)

[1] gemessen bei einem Raumwinkel Ω = 0.01 sr / measured at a solid angle of Ω = 0.01 sr

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Grenzwerte (T_A = 25 °C)
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op} , T_{stg}	– 40 … + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Vorwärtsgleichstrom Forward current	I_F	100	mA
Stoßstrom, t_p = 100 µs, D = 0 Surge current	I_{FSM}	1	A
Verlustleistung Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm^2 Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 16 mm^2 each	R_{thJA}	450	K/W

Kennwerte (T_A = 25 °C)
Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission I_F = 100 mA	λ_{peak}	860	nm
Schwerpunkt-Wellenlänge der Strahlung Centroid wavelength I_F = 100 mA	$\lambda_{centroid}$	850	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} I_F = 100 mA	$\Delta\lambda$	30	nm
Abstrahlwinkel Half angle	φ	± 13	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm^2
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3 × 0.3	mm²

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Kennwerte (T_A = 25 °C)
Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei I_F = 100 mA, R_L = 50 Ω Switching times, I_e from 10% to 90% and from 90% to 10%, I_F = 100 mA, R_L = 50 Ω	t_r, t_f	12	ns
Durchlassspannung Forward voltage I_F = 100 mA, t_p = 20 ms I_F = 1 A, t_p = 100 µs	 V_F V_F	 1.5 (< 1.8) 2.4 (< 3.0)	 V V
Sperrstrom Reverse current	I_R	not designed for reverse operation	µA
Gesamtstrahlungsfluss Total radiant flux I_F = 100 mA, t_p = 20 ms	$\Phi_{e\ typ}$	70	mW
Temperaturkoeffizient von I_e bzw. Φ_e, I_F = 100 mA Temperature coefficient of I_e or Φ_e, I_F = 100 mA	TC_I	– 0.5	%/K
Temperaturkoeffizient von V_F, I_F = 100 mA Temperature coefficient of V_F, I_F = 100 mA	TC_V	– 0.7	mV/K
Temperaturkoeffizient von λ, I_F = 100 mA Temperature coefficient of λ, I_F = 100 mA	TC_λ	+ 0.3	nm/K

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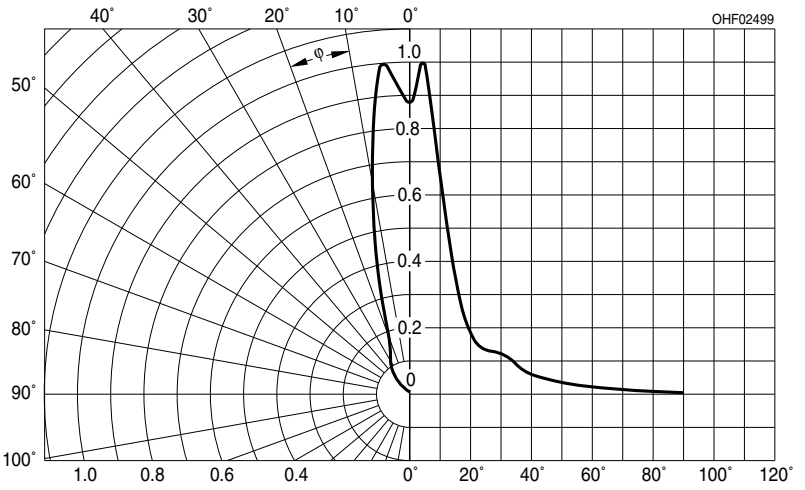
Strahlstärke I_e in Achsrichtung[1)]
gemessen bei einem Raumwinkel Ω = 0.01 sr
Radiant Intensity I_e in Axial Direction
at a solid angle of Ω = 0.01 sr

Bezeichnung Parameter	Symbol	Werte Values				Einheit Unit
		SFH 4350 -V	SFH 4350 -AW	SFH 4350 -BW	SFH 4350 -CW	
Strahlstärke Radiant intensity I_F = 100 mA, t_p = 20 ms	$I_{e\ min}$ $I_{e\ max}$	63 125	100 200	160 320	250 500	mW/sr mW/sr
Strahlstärke Radiant intensity I_F = 1 A, t_p = 25 µs	$I_{e\ typ}$	750	1200	1900	3000	mW/sr

[1)] Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1) /
Only one bin in one packing unit (variation lower 2:1)

Abstrahlcharakteristik
Radiation Characteristics $I_{rel} = f(\varphi)$



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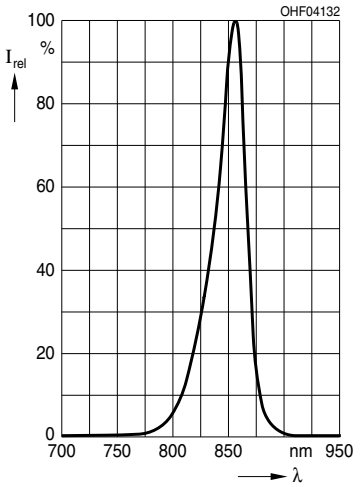
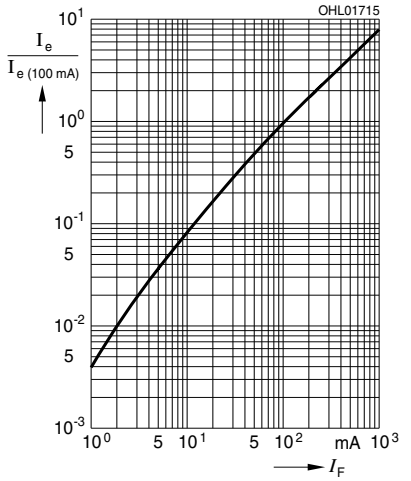
Relative Spectral Emission
$I_{rel} = f(\lambda)$

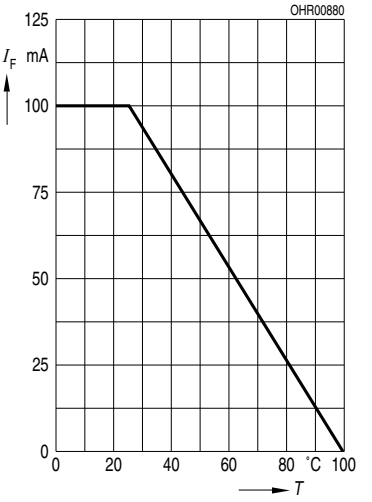


Radiant Intensity $\frac{I_e}{I_e\ 100\ mA} = f(I_F)$

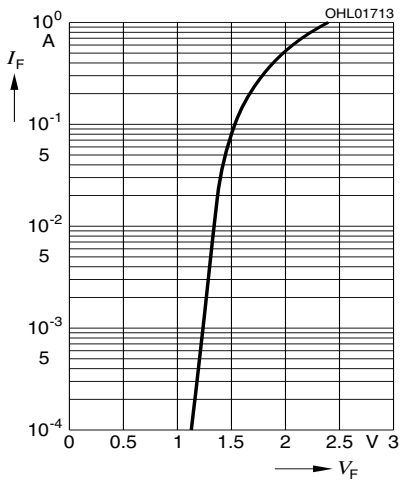
Single pulse, t_p = 25 µs



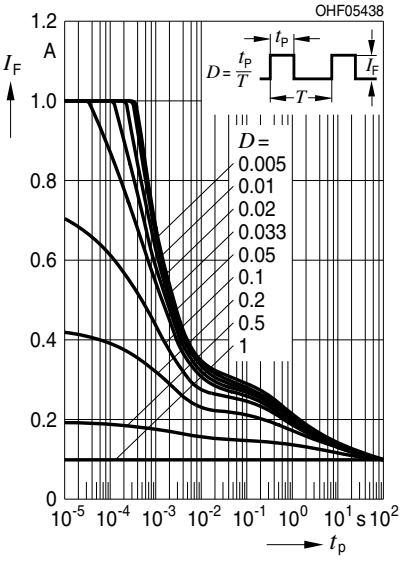
Max. Permissible Forward Current
$I_F = f(T_A)$, R_{thJA} = 450 K/W



Forward Current $I_F = f(V_F)$
Single pulse, t_p = 100 µs



Permissible Pulse Handling Capability $I_F = f(\tau)$, T_A = 25 °C, duty cycle D = parameter



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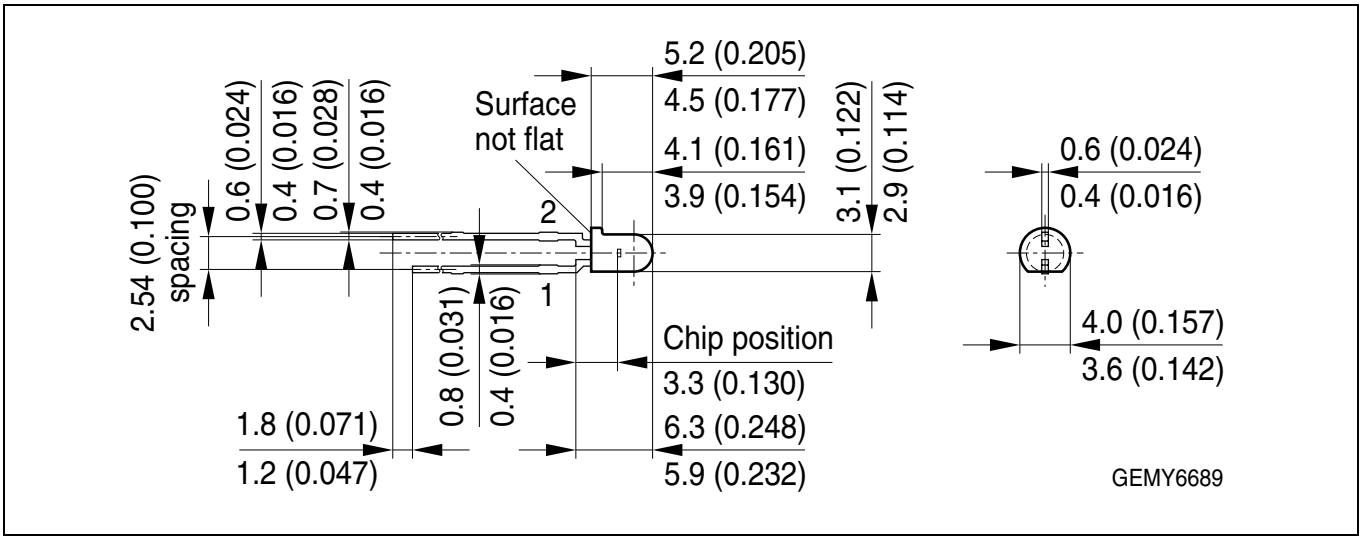
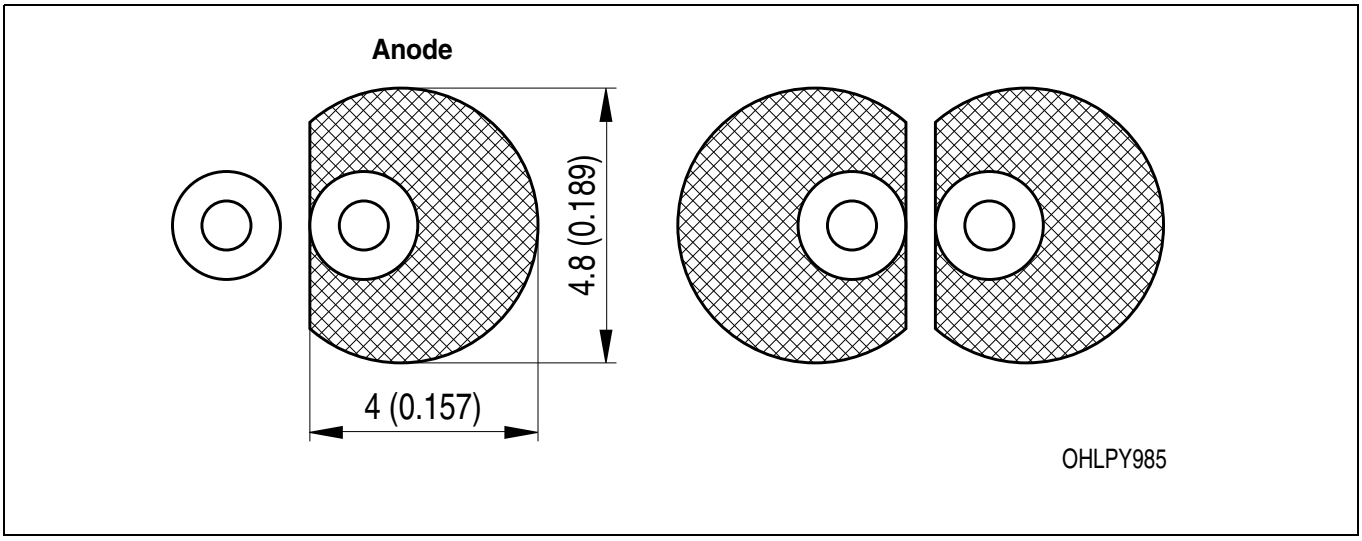
Maßzeichnung
Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

Gehäuse / Package	3 mm, klares Gehäuse / 1/10", clear package
Anschlussbelegung Pin configuration	1 = Anode / anode 2 = Kathode / cathode

Empfohlenes Lötpaddesign Wellenlöten TTW
Recommended Solder Pad Design TTW Soldering



Maße in mm (inch) / Dimensions in mm (inch).

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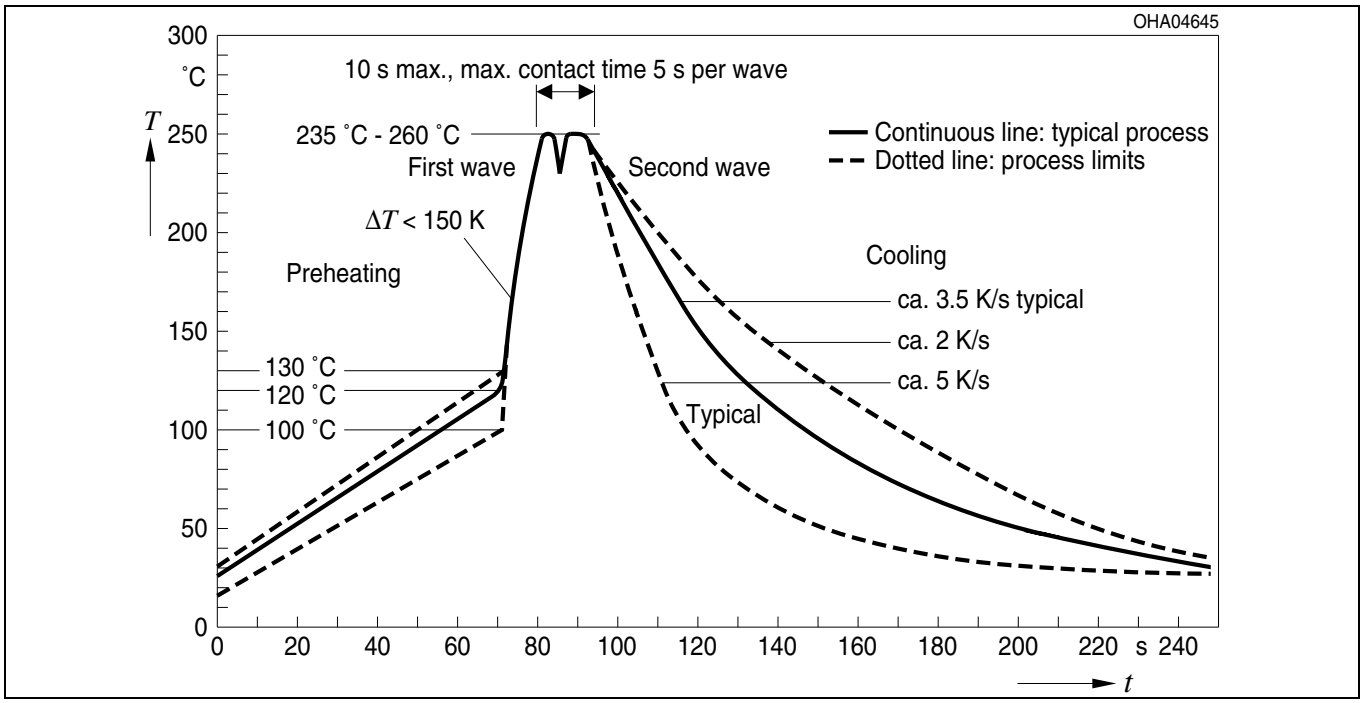
Lötbedingungen
Soldering Conditions
Wellenlöten (TTW) (nach IEC 61760-1)
TTW Soldering (acc. to IEC 61760-1)



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